



Property	Specification
Material	Multicrystalline Silicon
Type	P-type (Boron doped)
Resistivity	0.5 – 3.0 ohm-cm
Lifetime	$\geq 2\mu\text{s}$
Wafer Dimensions (W)	156 (± 0.5)mm
Squareness	90 ± 0.3 degrees
Thickness	$200.0\mu\text{m} \pm 20.0\mu\text{m}$
Chamfering Bevel Edge Width	0.5 - 2.0mm
T T V	$\leq 50.0\mu\text{m}$
Saw Marks	$\leq 20.0\mu\text{m}$
Bump/Step	$\leq 30\mu\text{m}$
Edge Defects	No V-type sharp chip
	No crack
	<2 per wafer 0.5 x 5.0mm
Appearance	No visible contamination, oil grease, soap or slurry stains
	Warpage Height < 150 μm
	No remarkable water mark
Crystal grain	Crystal grain $\leq 1\text{cm}^2$; <10 grains/cm ²
Impurities	Not seen by naked eyes (no pin hold)
B grade spec.	T = +60/-40 μm center 1 point check TTV $\leq 50\mu\text{m}$ 5 point check